

MOSFET – N-Channel, UltraFET Trench

200 V, 9.5 A, 200 mΩ

FDMC2610

General Description

This N-Channel MOSFET is a rugged gate version of onsemi's advanced POWERTRENCH® process. It has been optimized for power management applications.

Features

- Max $R_{DS(on)}$ = 200 mΩ at $V_{GS} = 10\text{ V}$, $I_D = 2.2\text{ A}$
- Max $R_{DS(on)}$ = 215 mΩ at $V_{GS} = 6\text{ V}$, $I_D = 1.5\text{ A}$
- Low Profile – 1 mm Max in a Power 33
- Pb-Free, Halide Free and RoHS Compliant

Applications

- DC-DC Conversion

MOSFET MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

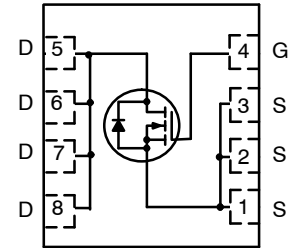
Symbol	Parameter	Value	Unit	
V_{DS}	Drain to Source Voltage	200	V	
V_{GS}	Gate to Source Voltage	±20	V	
I_D	Drain Current:		A	
	Continuous (Silicon limited)	$T_C = 25^\circ\text{C}$ 9.5		
	Continuous (Note 1a)	$T_A = 25^\circ\text{C}$ 2.2		
	Pulsed	15		
E_{AS}	Single Pulse Avalanche Energy (Note 3)	6	mJ	
P_D	Power Dissipation:	$T_C = 25^\circ\text{C}$	42	W
		$T_A = 25^\circ\text{C}$ (Note 1a)	2.1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

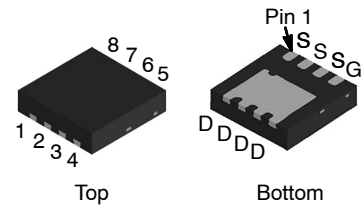
THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	60	

V_{DS}	$R_{DS(on)}$ MAX	I_D MAX
200 V	200 mΩ @ 10 V	9.5 A
	215 mΩ @ 6 V	

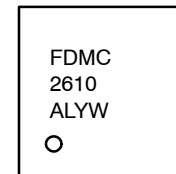


N-CHANNEL MOSFET



WDFN8 3.3 x 3.3, 0.65P
CASE 511DH

MARKING DIAGRAM



FDMC2610 = Specific Device Code
A = Assembly Site
L = Wafer Lot Number
YW = Assembly Start Week

ORDERING INFORMATION

Device	Package	Shipping†
FDMC2610	WDFN8 (Pb-Free, Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	200	–	–	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	199	–	mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 160 V, V _{GS} = 0 V	–	–	1	μA
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 125°C	–	–	100	
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	2	3.2	4	V
ΔV _{GS(th)} /ΔT _J	Gate to Source Threshold Voltage Temperature Coefficient	I _D = 250 μA, referenced to 25°C	–	–9.9	–	mV/°C
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10 V, I _D = 2.2 A	–	175	200	mΩ
		V _{GS} = 6 V, I _D = 1.5 A,	–	188	215	
		V _{GS} = 10 V, I _D = 2.2 A, T _J = 125°C	–	347	397	
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 2.2 A	–	7	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	–	720	960	pF
C _{oss}	Output Capacitance		–	41	55	pF
C _{rss}	Reverse Transfer Capacitance		–	12	20	pF
R _g	Gate Resistance	f = 1 MHz	–	0.7	–	Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 100 V, I _D = 2.2 A, V _{GS} = 10 V, R _{GEN} = 24 Ω	–	17	31	ns
t _r	Rise Time		–	13	24	ns
t _{d(off)}	Turn-Off Delay Time		–	29	47	ns
t _f	Fall Time		–	16	29	ns
Q _{g(TOT)}	Total Gate Charge at 10 V	V _{GS} = 0 V to 10 V, V _{DD} = 100 V, I _D = 2.2 A	–	12.3	18	nC
Q _{gs}	Gate to Source Gate Charge	V _{DD} = 100 V, I _D = 2.2 A	–	3	–	nC
Q _{gd}	Gate to Drain "Miller" Charge	V _{DD} = 100 V, I _D = 2.2 A	–	3.6	–	nC

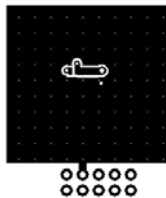
DRAIN-SOURCE DIODE CHARACTERISTICS

V _{SD}	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 2.2 A (Note 2)	–	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _F = 2.2 A, di/dt = 100 A/μs	–	69	104	ns
Q _{rr}	Reverse Recovery Charge		–	114	171	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

- R_{θJA} is determined with the device mounted on a 1 in² oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. R_{θJC} is guaranteed by design while R_{θCA} is determined by the user's board design.



- a) 60°C/W when mounted on a 1 in² pad of 2 oz copper.



- b) 135°C/W when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
- Starting T_J = 25°C; N-ch: L = 3 mH, I_{AS} = 2 A, V_{DD} = 200 V, V_{GS} = 10 V.

TYPICAL CHARACTERISTICS

($T_J = 25^\circ\text{C}$ unless otherwise noted)

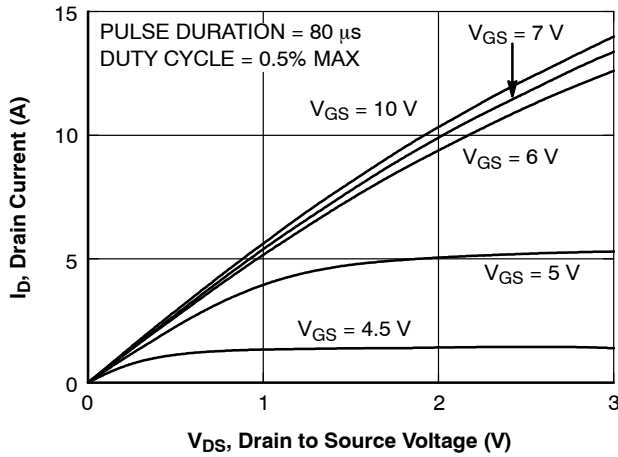


Figure 1. On-Region Characteristics

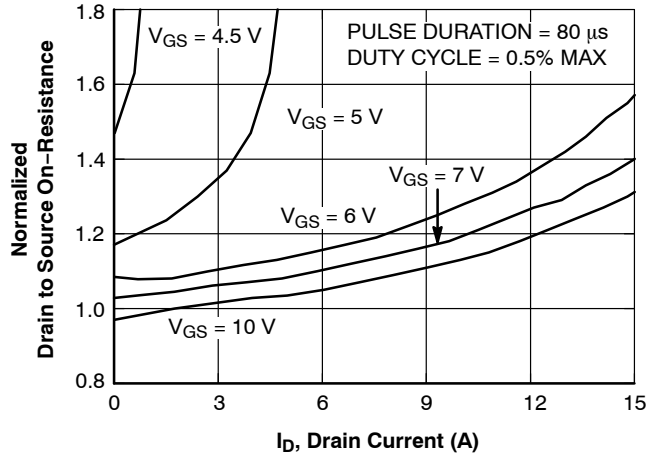


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

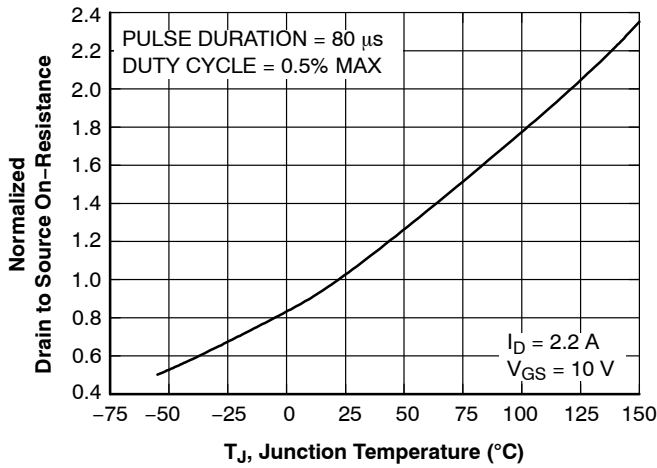


Figure 3. Normalized On-Resistance vs. Junction Temperature

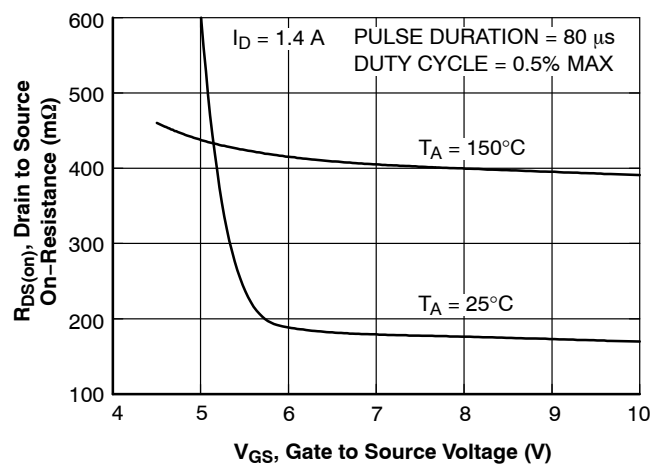


Figure 4. On-Resistance vs. Gate to Source Voltage

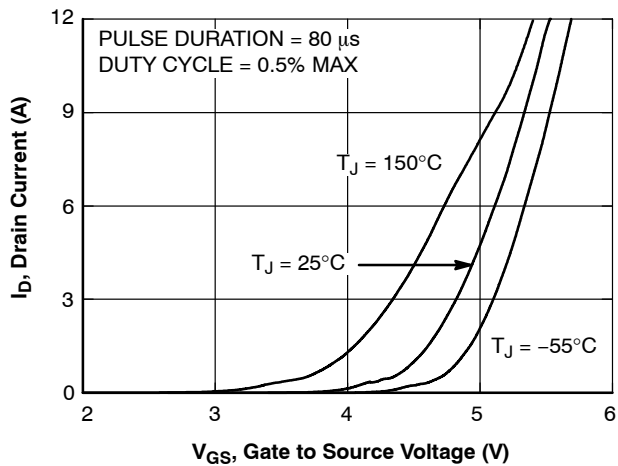


Figure 5. Transfer Characteristics

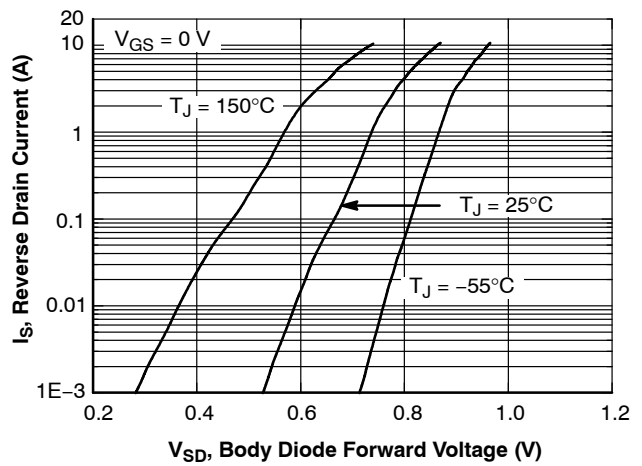


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

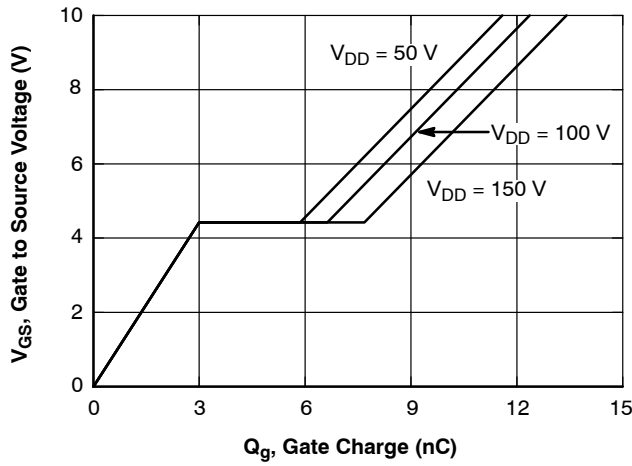


Figure 7. Gate Charge Characteristics

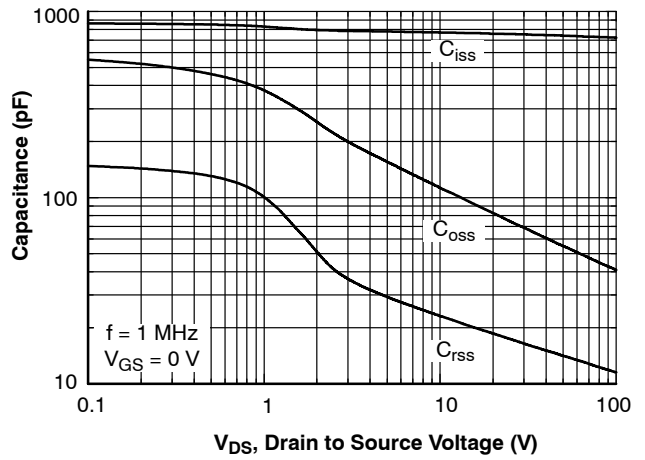


Figure 8. Capacitance vs. Drain to Source Voltage

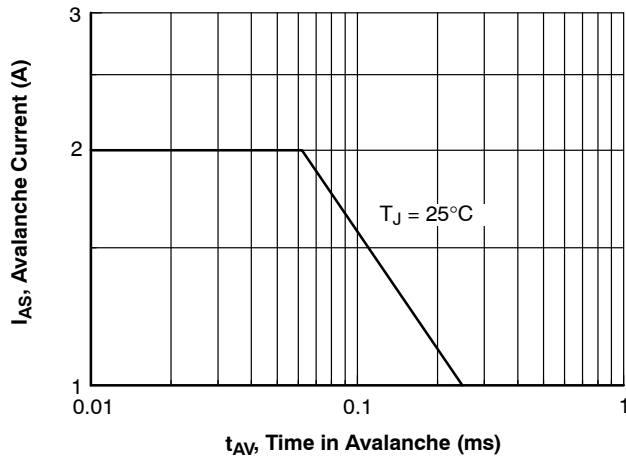


Figure 9. Unclamped Inductive Switching Capability

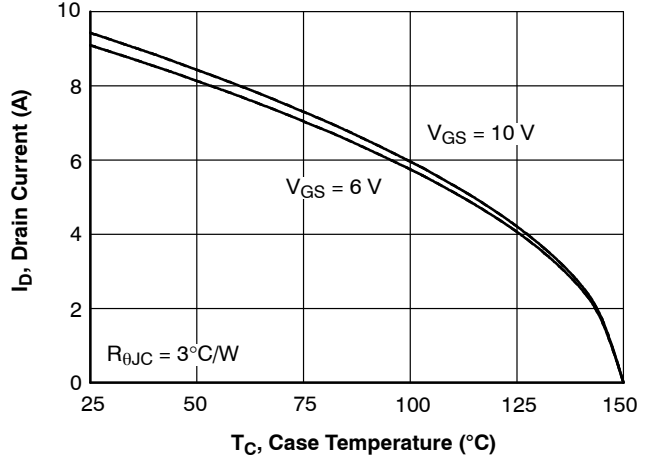


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

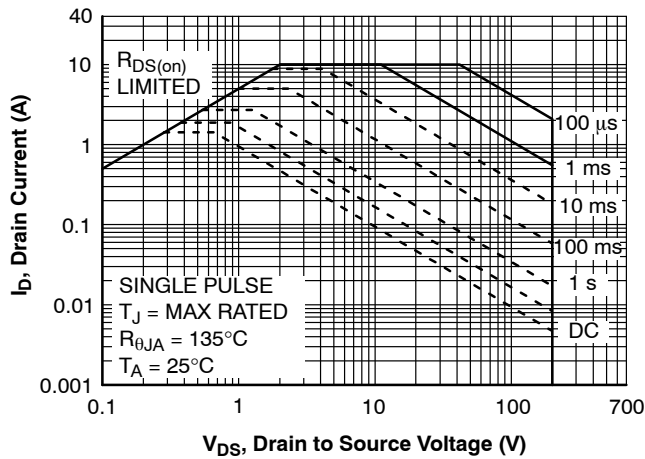


Figure 11. Forward Bias Safe Operating Area

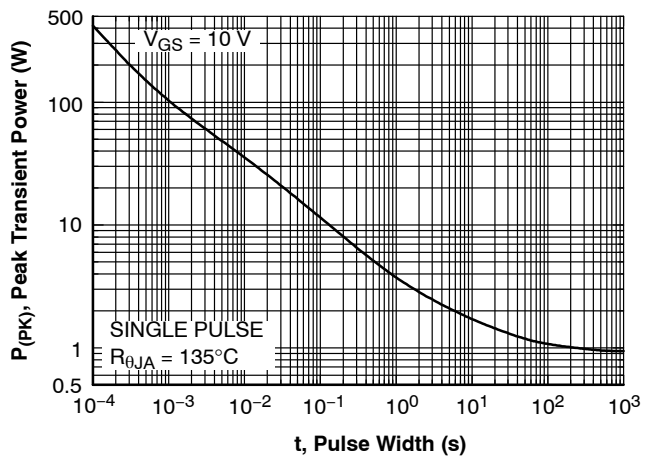


Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

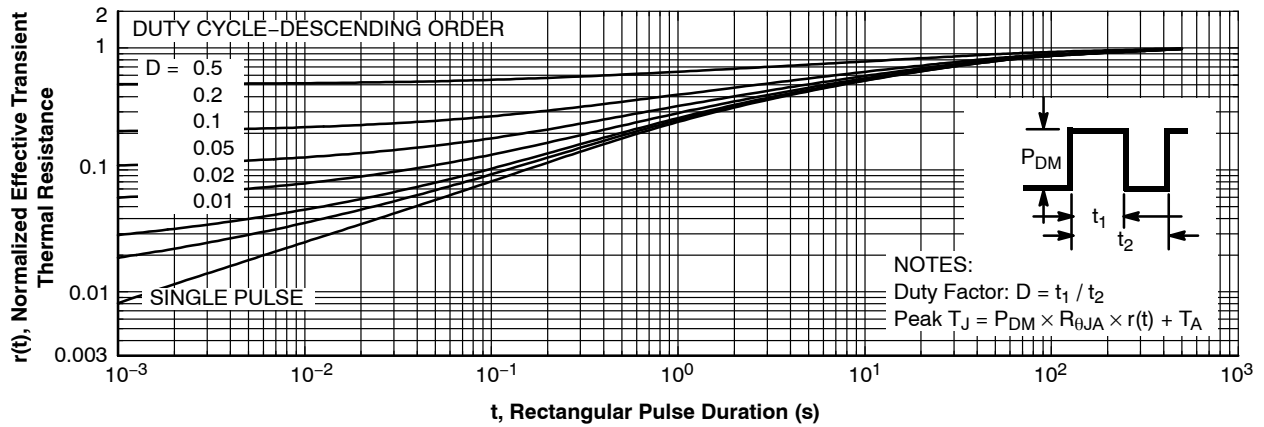


Figure 13. Transient Thermal Response Curve

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